

### REMARKS

Claims 1 and 2 stand rejected under 35 U.S.C. 102 (e) as being anticipated by U.S. Pat. No. 6,165,808 to Zhang (hereinafter "Zhang"). Claims 3-17 stand rejected under 35 U.S.C. 103 (a) as being unpatentable over Zhang in view of U.S. Pat. No. 5,779,514 to Cheng et al. (hereinafter "Cheng"). For purposes of efficiency, the two rejections will be discussed together as it appears there is some misunderstanding with respect to the claimed invention and the cited references.

As an initial matter, with respect to claims 1 and 2, Zhang simply discloses a process for sharpening a tapered silicon structure (see Zhang, Figures 3a-3c) by employing a chemical oxidant only (see Zhang, Column 5, lines 47-55) to form a thin oxide layer in a fixed thickness range of about 20Å to 40Å (see Zhang, Column 5, lines 54-56 and Column 7, lines 53-58). Moreover, as described in Zhang, if a pointed (or finished) silicon structure is needed (as described in Zhang at Column 6, lines 41-44), the oxidation step (performed by employing the chemical oxidant) has to be repeated (as shown in Zhang at Figures 4(a) - 4(f) and described in Column 8, lines 29-32). This means that the oxidation disclosed in Zhang should be processed more than one time for forming a pointed silicon structure.

With respect to claims 3-17, not only does Zhang fail to disclose the elements of claims 1 and 2, it also fails to disclose the elements of claims 3-17. Cheng does not disclose the claimed elements that Zhang fails to disclose. Accordingly, the claimed invention is not unpatentable over Zhang in view of Cheng.

With respect to claims 3-8 in particular, although Cheng arguably discloses the step of removing the remained photoresist, it is silent on the anodic oxidation method and the oxidation. Thus, even if one having ordinary skill in

the art combines Zhang and Cheng, it is still apparent that the anodic oxidation method is not disclosed thereby.

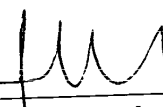
With respect to Claims 9-17, even if Cheng is considered to disclose the steps of removing the remained mask units and photoresist and forming a second metal layer, as set forth by the Examiner, the disclosure of the anodic oxidation method is distinguishable therefrom. Furthermore, even though a second metal layer is formed on the structure in Fig. 4(e) of Zhang, the combined structure formed by combining the steps of the two cited references will still be different from the structure shown in Fig. 4(h) of the claimed invention. That is because, in fact, when the step of removing the remained mask units or photoresist in Cheng (as mentioned by the Examiner) is performed, **the silicon** (namely the substrate) and **the silicon dioxide** (namely the mask) will **simultaneously be removed in one step** (see step (e) in Claim 1, Column 3, line 51-66, step (g) in Claim 7, and Column 4, lines 37-48). Therefore, even when combining the steps of the two cited references the structure formed thereby is still significantly different from the claimed invention.

**Applicant:** Cheng et al.  
**Application No.:** 09/925,356

For the above reasons, Applicant respectfully submits that the presently claimed invention is patentable over the prior art. Reconsideration and allowance of the claims is respectfully requested.

Respectfully submitted,

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Enclosure (1)